





EC26 20

Series — RoHS Compliant (Pb-free) 3.3V 4 Pad 5mm x 7mm Ceramic SMD LVCMOS Oscillator

Frequency Tolerance/Stability ±20ppm Maximum

Operating Temperature Range --10°C to +70°C

T TS -12.288M

Nominal Frequency 12.288MHz

Pin 1 Connection
Tri-State (High Impedance)

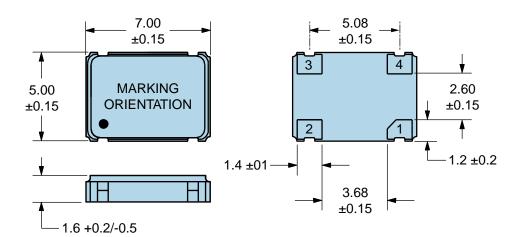
Duty Cycle 50 ±5(%)

| Nominal Frequency 12.288MHz Frequency Tolerance/Stability ±20ppm Maximum (Inclusive of all conditions: Calibration Tolerance at 25°C, Frequency Stability over the Operating Temperature Range, Supply Voltage Change, Ouput Load Change, First Year Aging at 25°C, Shock, and Vibration) Operating Temperature Range ±10°C to +70°C Supply Voltage 3.3Vdc ±10% Input Current 10mA Maximum Output Voltage Logic High (Voh) 90% of Vdd Minimum (IOL=+8mA) Output Voltage Logic Low (Vol) 10% of Vdd Maximum (IOL=+8mA) Rise/Fall Time 5nSec Maximum (w/15pF Load), 7nSec Maximum (w/30pF Load) (Measured at 20% to 80% of waveform) Duty Cycle 50 ±5(%) (Measured at 50% of waveform) Load Drive Capability 30pF Maximum Output Logic Type CMOS Pin 1 Connection Tri-State (High Impedance) Tri-State Input Voltage (Vih and Vii) +0.7Vdd Minimum or No Connect to Enable Output, +0.3Vdd Maximum to Disable Output (High Impedance) Standby Current 10µA Maximum (Disabled Output: High Impedance) RMS Phase Jitter 1pSec Maximum (12kHz to 20MHz offset frequency) Start Up Time 10mSec Maximum Storage Temperature Range -55°C to +125°C | ELECTRICAL SPECIFICATIONS | | |
|--|---------------------------------------|--|--|
| Operating Temperature Range, Supply Voltage Change, Ouput Load Change, First Year Aging at 25°C, Shock, and Vibration) Operating Temperature Range -10°C to +70°C Supply Voltage 3.3Vdc ±10% Input Current 10mA Maximum Output Voltage Logic High (Voh) 90% of Vdd Minimum (IOH=-8mA) Output Voltage Logic Low (Vol) 10% of Vdd Maximum (IOL=+8mA) Rise/Fall Time 5nSec Maximum (w/15pF Load), 7nSec Maximum (w/30pF Load) (Measured at 20% to 80% of waveform) Duty Cycle 50 ±5(%) (Measured at 50% of waveform) Load Drive Capability 30pF Maximum Output Logic Type CMOS Pin 1 Connection Tri-State (High Impedance) Tri-State Input Voltage (Vih and Vil) Impedance) Standby Current 10µA Maximum (Disabled Output: High Impedance) RMS Phase Jitter 10mSec Maximum 10mSec Maximum 10mSec Maximum | Nominal Frequency | 12.288MHz | |
| Supply Voltage 3.3Vdc ±10% Input Current 10mA Maximum Output Voltage Logic High (Voh) 90% of Vdd Minimum (IOH=-8mA) Output Voltage Logic Low (Vol) 10% of Vdd Maximum (IOL=+8mA) Rise/Fall Time 5nSec Maximum (w/15pF Load), 7nSec Maximum (w/30pF Load) (Measured at 20% to 80% of waveform) Duty Cycle 50 ±5(%) (Measured at 50% of waveform) Load Drive Capability 30pF Maximum Output Logic Type CMOS Pin 1 Connection Tri-State (High Impedance) Tri-State Input Voltage (Vih and Vil) +0.7Vdd Minimum or No Connect to Enable Output, +0.3Vdd Maximum to Disable Output (High Impedance) Standby Current 10μA Maximum (Disabled Output: High Impedance) RMS Phase Jitter 1pSec Maximum (12kHz to 20MHz offset frequency) Start Up Time 10mSec Maximum | Frequency Tolerance/Stability | Operating Temperature Range, Supply Voltage Change, Ouput Load Change, First Year Aging at 25°C, | |
| Input Current Output Voltage Logic High (Voh) 90% of Vdd Minimum (IOH=-8mA) Output Voltage Logic Low (Vol) 10% of Vdd Maximum (IOL=+8mA) Rise/Fall Time 5nSec Maximum (w/15pF Load), 7nSec Maximum (w/30pF Load) (Measured at 20% to 80% of waveform) Duty Cycle 50 ±5(%) (Measured at 50% of waveform) Load Drive Capability 30pF Maximum Output Logic Type CMOS Pin 1 Connection Tri-State (High Impedance) Tri-State Input Voltage (Vih and Vil) h-0.7Vdd Minimum or No Connect to Enable Output, +0.3Vdd Maximum to Disable Output (High Impedance) Standby Current 10μA Maximum (Disabled Output: High Impedance) RMS Phase Jitter 1pSec Maximum (12kHz to 20MHz offset frequency) Start Up Time 10mSec Maximum | Operating Temperature Range | -10°C to +70°C | |
| Output Voltage Logic High (Voh) Output Voltage Logic Low (Vol) 10% of Vdd Maximum (IOL=+8mA) Rise/Fall Time 5nSec Maximum (w/15pF Load), 7nSec Maximum (w/30pF Load) (Measured at 20% to 80% of waveform) Duty Cycle 50 ±5(%) (Measured at 50% of waveform) Load Drive Capability 30pF Maximum Output Logic Type CMOS Pin 1 Connection Tri-State (High Impedance) Tri-State Input Voltage (Vih and Vil) +0.7Vdd Minimum or No Connect to Enable Output, +0.3Vdd Maximum to Disable Output (High Impedance) Standby Current 10µA Maximum (Disabled Output: High Impedance) RMS Phase Jitter 1pSec Maximum (12kHz to 20MHz offset frequency) Start Up Time 10mSec Maximum | Supply Voltage | 3.3Vdc ±10% | |
| Output Voltage Logic Low (Vol) 10% of Vdd Maximum (IOL=+8mA) Rise/Fall Time 5nSec Maximum (w/15pF Load), 7nSec Maximum (w/30pF Load) (Measured at 20% to 80% of waveform) Duty Cycle 50 ±5(%) (Measured at 50% of waveform) Load Drive Capability 30pF Maximum Output Logic Type CMOS Pin 1 Connection Tri-State (High Impedance) Tri-State Input Voltage (Vih and Vil) +0.7Vdd Minimum or No Connect to Enable Output, +0.3Vdd Maximum to Disable Output (High Impedance) Standby Current 10μA Maximum (Disabled Output: High Impedance) RMS Phase Jitter 1pSec Maximum (12kHz to 20MHz offset frequency) Start Up Time 10mSec Maximum | Input Current | 10mA Maximum | |
| Rise/Fall Time 5nSec Maximum (w/15pF Load), 7nSec Maximum (w/30pF Load) (Measured at 20% to 80% of waveform) Duty Cycle 50 ±5(%) (Measured at 50% of waveform) Load Drive Capability 30pF Maximum Output Logic Type CMOS Pin 1 Connection Tri-State (High Impedance) Tri-State Input Voltage (Vih and Vil) +0.7Vdd Minimum or No Connect to Enable Output, +0.3Vdd Maximum to Disable Output (High Impedance) Standby Current 10µA Maximum (Disabled Output: High Impedance) RMS Phase Jitter 1pSec Maximum (12kHz to 20MHz offset frequency) Start Up Time 10mSec Maximum | Output Voltage Logic High (Voh) | 90% of Vdd Minimum (IOH=-8mA) | |
| Duty Cycle 50 ±5(%) (Measured at 50% of waveform) Load Drive Capability 30pF Maximum Output Logic Type CMOS Pin 1 Connection Tri-State (High Impedance) Tri-State Input Voltage (Vih and Vil) +0.7Vdd Minimum or No Connect to Enable Output, +0.3Vdd Maximum to Disable Output (High Impedance) Standby Current 10μA Maximum (Disabled Output: High Impedance) RMS Phase Jitter 1pSec Maximum (12kHz to 20MHz offset frequency) Start Up Time 10mSec Maximum | Output Voltage Logic Low (Vol) | 10% of Vdd Maximum (IOL=+8mA) | |
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| Output Logic Type CMOS Pin 1 Connection Tri-State (High Impedance) Tri-State Input Voltage (Vih and Vil) +0.7Vdd Minimum or No Connect to Enable Output, +0.3Vdd Maximum to Disable Output (High Impedance) Standby Current 10µA Maximum (Disabled Output: High Impedance) RMS Phase Jitter 1pSec Maximum (12kHz to 20MHz offset frequency) Start Up Time 10mSec Maximum | Duty Cycle | 50 ±5(%) (Measured at 50% of waveform) | |
| Pin 1 Connection Tri-State (High Impedance) Tri-State Input Voltage (Vih and Vil) +0.7Vdd Minimum or No Connect to Enable Output, +0.3Vdd Maximum to Disable Output (High Impedance) Standby Current 10µA Maximum (Disabled Output: High Impedance) RMS Phase Jitter 1pSec Maximum (12kHz to 20MHz offset frequency) Start Up Time 10mSec Maximum | Load Drive Capability | 30pF Maximum | |
| Tri-State Input Voltage (Vih and Vil) +0.7Vdd Minimum or No Connect to Enable Output, +0.3Vdd Maximum to Disable Output (High Impedance) Standby Current 10µA Maximum (Disabled Output: High Impedance) RMS Phase Jitter 1pSec Maximum (12kHz to 20MHz offset frequency) Start Up Time 10mSec Maximum | Output Logic Type | CMOS | |
| Impedance) Standby Current 10μA Maximum (Disabled Output: High Impedance) RMS Phase Jitter 1pSec Maximum (12kHz to 20MHz offset frequency) Start Up Time 10mSec Maximum | Pin 1 Connection | Tri-State (High Impedance) | |
| RMS Phase Jitter 1pSec Maximum (12kHz to 20MHz offset frequency) Start Up Time 10mSec Maximum | Tri-State Input Voltage (Vih and Vil) | | |
| Start Up Time 10mSec Maximum | Standby Current | 10μA Maximum (Disabled Output: High Impedance) | |
| • | RMS Phase Jitter | 1pSec Maximum (12kHz to 20MHz offset frequency) | |
| Storage Temperature Range -55°C to +125°C | Start Up Time | 10mSec Maximum | |
| | Storage Temperature Range | -55°C to +125°C | |

| ENVIRONMENTAL & MECHANICAL SPECIFICATIONS | | |
|---|---|--|
| ESD Susceptibility | MIL-STD-883, Method 3015, Class 1, HBM: 1500V | |
| Fine Leak Test | MIL-STD-883, Method 1014, Condition A | |
| Flammability | UL94-V0 | |
| Gross Leak Test | MIL-STD-883, Method 1014, Condition C | |
| Mechanical Shock | MIL-STD-883, Method 2002, Condition B | |
| Moisture Resistance | MIL-STD-883, Method 1004 | |
| Moisture Sensitivity | J-STD-020, MSL 1 | |
| Resistance to Soldering Heat | MIL-STD-202, Method 210, Condition K | |
| Resistance to Solvents | MIL-STD-202, Method 215 | |
| Solderability | MIL-STD-883, Method 2003 | |
| Temperature Cycling | MIL-STD-883, Method 1010, Condition B | |
| Vibration | MIL-STD-883, Method 2007, Condition A | |



MECHANICAL DIMENSIONS (all dimensions in millimeters)



| PIN | CONNECTION |
|-----|--------------------|
| 1 | Tri-State |
| 2 | Ground/Case Ground |
| 3 | Output |
| 4 | Supply Voltage |

| LINE | MARKING |
|------|---|
| 1 | ECLIPTEK |
| 2 | 12.288M |
| 3 | XXYZZ XX=Ecliptek Manufacturing Code Y=Last Digit of the Year ZZ=Week of the Year |

Suggested Solder Pad Layout

All Dimensions in Millimeters



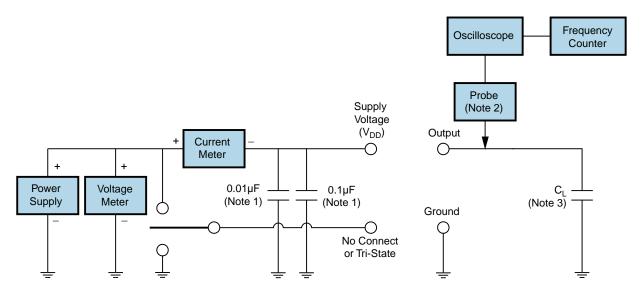
All Tolerances are ±0.1



OUTPUT WAVEFORM & TIMING DIAGRAM



Test Circuit for CMOS Output



- Note 1: An external $0.1\mu F$ low frequency tantalum bypass capacitor in parallel with a $0.01\mu F$ high frequency ceramic bypass capacitor close to the package ground and V_{DD} pin is required.
- Note 2: A low capacitance (<12pF), 10X attenuation factor, high impedance (>10Mohms), and high bandwidth (>300MHz) passive probe is recommended.
- Note 3: Capacitance value \dot{C}_L includes sum of all probe and fixture capacitance.



Recommended Solder Reflow Methods



High Temperature Infrared/Convection

| <u> </u> | |
|---|---|
| T _s MAX to T _∟ (Ramp-up Rate) | 3°C/second Maximum |
| Preheat | |
| - Temperature Minimum (Ts MIN) | 150°C |
| - Temperature Typical (T _s TYP) | 175°C |
| - Temperature Maximum (T _s MAX) | 200°C |
| - Time (t _s MIN) | 60 - 180 Seconds |
| Ramp-up Rate (T _L to T _P) | 3°C/second Maximum |
| Time Maintained Above: | |
| - Temperature (T∟) | 217°C |
| - Time (t∟) | 60 - 150 Seconds |
| Peak Temperature (T _P) | 260°C Maximum for 10 Seconds Maximum |
| Target Peak Temperature (T _P Target) | 250°C +0/-5°C |
| Time within 5°C of actual peak (tp) | 20 - 40 seconds |
| Ramp-down Rate | 6°C/second Maximum |
| Time 25°C to Peak Temperature (t) | 8 minutes Maximum |
| Moisture Sensitivity Level | Level 1 |
| Additional Notes | Temperatures shown are applied to body of device. |
| | |



Recommended Solder Reflow Methods



Low Temperature Infrared/Convection 240°C

| T _S MAX to T _L (Ramp-up Rate) | 5°C/second Maximum |
|---|--|
| Preheat | |
| - Temperature Minimum (T _s MIN) | N/A |
| - Temperature Typical (T _S TYP) | 150°C |
| - Temperature Maximum (T _s MAX) | N/A |
| - Time (t _s MIN) | 60 - 120 Seconds |
| Ramp-up Rate (T _L to T _P) | 5°C/second Maximum |
| Time Maintained Above: | |
| - Temperature (T∟) | 150°C |
| - Time (t∟) | 200 Seconds Maximum |
| Peak Temperature (T _P) | 240°C Maximum |
| Target Peak Temperature (T _P Target) | 240°C Maximum 1 Time / 230°C Maximum 2 Times |
| Time within 5°C of actual peak (tp) | 10 seconds Maximum 2 Times / 80 seconds Maximum 1 Time |
| Ramp-down Rate | 5°C/second Maximum |
| Time 25°C to Peak Temperature (t) | N/A |
| Moisture Sensitivity Level | Level 1 |
| Additional Notes | Temperatures shown are applied to body of device. |

Low Temperature Manual Soldering

185°C Maximum for 10 seconds Maximum, 2 times Maximum. (Temperatures shown are applied to body of device.)

High Temperature Manual Soldering

260°C Maximum for 5 seconds Maximum, 2 times Maximum. (Temperatures shown are applied to body of device.)